

2.5V 至 3.3V 高性能时钟缓冲器

查询样品: **CDCVF2310-EP**

特性

- 高性能 **1:10** 时钟驱动器
- 在 V_{DD} 为 **3.3V** 时, 运行频率高达 **200MHz**
- 在 V_{DD} 为 **3.3V** 时, 引脚到引脚偏斜小于 **100ps**
- V_{DD} 范围: **2.3V 至 3.6V**
- 输出使能毛刺脉冲抑制
- 将一个时钟输入分频至五个输出的两个组
- **25Ω** 片载串联阻尼电阻器
- 采用 **24** 引脚薄型小尺寸封装 (**TSSOP**)

应用范围

- 通用应用

支持国防、航空航天、和医疗应用

- 受控基线
- 一个组装和测试场所
- 一个制造场所
- 支持军用 (**-55°C 至 125°C**) 温度范围 ⁽¹⁾
- 延长的产品生命周期
- 延长的产品变更通知
- 产品可追溯性

(1) 可定制工作温度范围

说明

CDCVF2310 是一款运行频率高达 200MHz 的高性能、低偏斜时钟缓冲器。五个输出的两个组中的每一个组提供 CLK 的低偏斜副本。加电后, 无论控制引脚的状态如何, 输出的缺省状态为低电平。对于正常运行, 当控制引脚 (分别为 **1G** 或 **2G**) 被保持在低电平并且在 CLK 输入上检测到一个负时钟边沿时, 组 **1Y[0:4]** 或 **2Y[0:4]** 的输出可被置于低电平状态。当控制引脚 (**1G** 和 **2G**) 被保持在高电平并且在 CLK 输入上检测到一个负时钟边沿时, 组 **1Y[0:4]** 或 **2Y[0:4]** 的输出可被切换至缓冲器模式。此器件运行在一个 2.5V 和 3.3V 环境中。内置的输出使能毛刺脉冲抑制可确保一个已同步的输出使能序列以分配完全周期时钟信号。

CDCVF2310 运行温度范围为 -55°C 至 125°C。

Table 1. ORDERING INFORMATION⁽¹⁾

T_J	PACKAGE	ORDERABLE PART NUMBER	TOP-SIDE MARKING	VID NUMBER
-55°C to 125°C	TSSOP - PW	CDCVF2310MPWREP	CKV2310EP	V62/13603-01XE
		CDCVF2310MPWEP	CKV2310EP	V62/13603-01XE-T

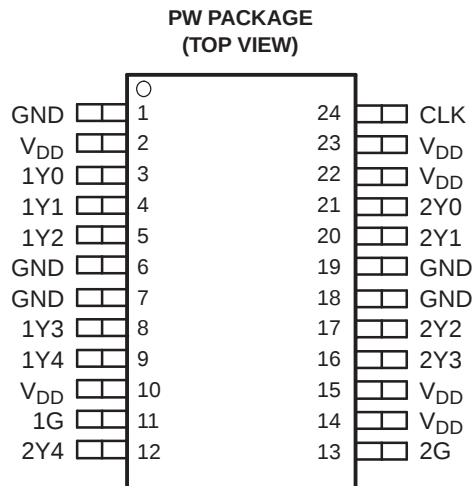
(1) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI Web site at www.ti.com.



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PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of the Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.

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English Data Sheet: **SCAS934**





This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

FUNCTIONAL BLOCK DIAGRAM

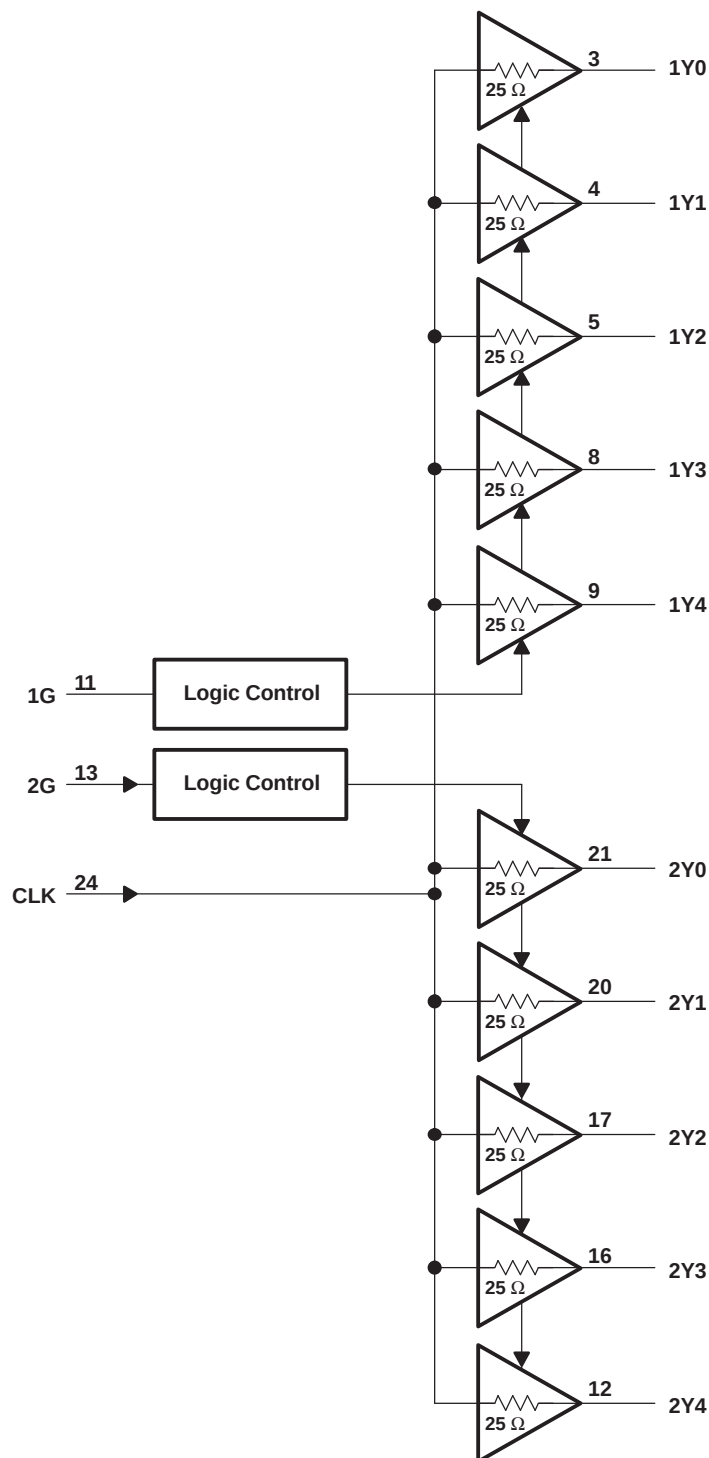


Table 2. FUNCTION TABLE

INPUT			OUTPUT	
1G	2G	CLK	1Y[0:4]	2Y[0:4]
L	L	↓	L	L
H	L	↓	CLK ⁽¹⁾	L
L	H	↓	L	CLK ⁽¹⁾
H	H	↓	CLK ⁽¹⁾	CLK ⁽¹⁾

- (1) After detecting one negative edge on the CLK input, the output follows the input CLK if the control pin is held high.

Terminal Functions

TERMINAL		I/O	DESCRIPTION
NAME	NO.		
1G	11	I	Output enable control for 1Y[0:4] outputs. This output enable is active-high, meaning the 1Y[0:4] clock outputs follow the input clock (CLK) if this pin is logic high.
2G	13	I	Output enable control for 2Y[0:4] outputs. This output enable is active-high, meaning the 2Y[0:4] clock outputs follow the input clock (CLK) if this pin is logic high.
1Y[0:4]	3, 4, 5, 8, 9	O	Buffered output clocks
2Y[0:4]	21, 20, 17, 16, 12	O	Buffered output clocks
CLK	24	I	Input reference frequency
GND	1, 6, 7, 18, 19		Ground
V _{DD}	2, 10, 14, 15, 22, 23		DC power supply, 2.3 V – 3.6 V

ABSOLUTE MAXIMUM RATINGS

over operating junction temperature range (unless otherwise noted) ⁽¹⁾

Supply voltage range, V _{DD}	–0.5 V to 4.6 V
Input voltage range, V _I ⁽²⁾ ⁽³⁾	–0.5 V to V _{DD} + 0.5 V
Output voltage range, V _O ⁽²⁾ ⁽³⁾	–0.5 V to V _{DD} + 0.5 V
Input clamp current, I _{IK} (V _I < 0 or V _I > V _{DD})	±50 mA
Output clamp current, I _{OK} (V _O < 0 or V _O > V _{DD})	±50 mA
Continuous total output current, I _O (V _O = 0 to V _{DD})	±50 mA
Storage temperature range T _{stg}	–65°C to 150°C

- (1) Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) The input and output negative voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
- (3) This value is limited to 4.6 V maximum.

THERMAL INFORMATION

THERMAL METRIC ⁽¹⁾		CDCVF2310	UNITS
		PW	
		24 PINS	
θ_{JA}	Junction-to-ambient thermal resistance ⁽²⁾	91.7	°C/W
θ_{JCTop}	Junction-to-case (top) thermal resistance ⁽³⁾	31.2	
θ_{JB}	Junction-to-board thermal resistance ⁽⁴⁾	46.4	
ψ_{JT}	Junction-to-top characterization parameter ⁽⁵⁾	1.5	
ψ_{JB}	Junction-to-board characterization parameter ⁽⁶⁾	45.8	
θ_{JBot}	Junction-to-case (bottom) thermal resistance ⁽⁷⁾	N/A	

- (1) 有关传统和新的热 度量的更多信息，请参阅 *IC 封装热量应用报告*，[SPRA953](#)。
- (2) 在 JESD51-2a 描述的环境中，按照 JESD51-7 的指定，在一个 JEDEC 标准高 K 电路板上进行仿真，从而获得自然 对流条件下的结至环境热阻。
- (3) 通过在封装顶部模拟一个冷板测试来获得结至芯片外壳（顶部）的热阻。不存在特定的 JEDEC 标准测试，但 可在 ANSI SEMI 标准 G30-88 中找到内容接近的说明。
- (4) 按照 JESD51-8 中的说明，通过 在配有用于控制 PCB 温度的环形冷板夹具的环境中进行仿真，以获得结板热阻。
- (5) 结至顶部特征参数， ψ_{JT} ，估算真实系统中器件的结温，并使用 JESD51-2a（第 6 章和第 7 章）中 描述的程序从仿真数据中 提取出该参数以便获得 θ_{JA} 。
- (6) 结至电路板特征参数， ψ_{JB} ，估算真实系统中器件的结温，并使用 JESD51-2a（第 6 章和第 7 章）中 描述的程序从仿真数据中 提取出该参数以便获得 θ_{JA} 。
- (7) 通过在外露（电源）焊盘上进行冷板测试仿真来获得 结至芯片外壳（底部）热阻。不存在特定的 JEDEC 标准 测试，但可在 ANSI SEMI 标准 G30-88 中找到内容接近的说明。

RECOMMENDED OPERATING CONDITIONS ⁽¹⁾

		MIN	NOM	MAX	UNIT
Supply voltage, V_{DD}		2.3	2.5		V
			3.3	3.6	
Low-level input voltage, V_{IL}	$V_{DD} = 3\text{ V to }3.6\text{ V}$			0.8	V
	$V_{DD} = 2.3\text{ V to }2.7\text{ V}$			0.7	
High-level input voltage, V_{IH}	$V_{DD} = 3\text{ V to }3.6\text{ V}$	2			V
	$V_{DD} = 2.3\text{ V to }2.7\text{ V}$	1.7			
Input voltage, V_I		0		V_{DD}	V
High-level output current, I_{OH}	$V_{DD} = 3\text{ V to }3.6\text{ V}$			12	mA
	$V_{DD} = 2.3\text{ V to }2.7\text{ V}$			6	
Low-level output current, I_{OL}	$V_{DD} = 3\text{ V to }3.6\text{ V}$			12	mA
	$V_{DD} = 2.3\text{ V to }2.7\text{ V}$			6	
Operating junction temperature, T_J		-55		125	°C

- (1) Unused inputs must be held high or low to prevent them from floating.

ELECTRICAL CHARACTERISTICS

over recommended operating junction temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP ⁽¹⁾	MAX	UNIT
V _{IK}	Input voltage	V _{DD} = 3 V, I _I = −18 mA				−1.2	V
I _I	Input current	V _I = 0 V or V _{DD}				±5	μA
I _{DD} ⁽²⁾	Static device current	CLK = 0 V or V _{DD} , I _O = 0 mA				100	μA
C _I	Input capacitance	V _{DD} = 2.3 V to 3.6 V, V _I = 0 V or V _{DD}			2.5		pF
C _O	Output capacitance	V _{DD} = 2.3 V to 3.6 V, V _I = 0 V or V _{DD}			2.8		pF
V _{DD} = 3.3 V ±0.3 V							
V _{OH}	High-level output voltage	V _{DD} = min to max, I _{OH} = −100 μA		V _{DD} − 0.2		V	
		V _{DD} = 3 V	I _{OH} = −12 mA	2.1			
			I _{OH} = −6 mA	2.4			
V _{OL}	Low-level output voltage	V _{DD} = min to max, I _{OL} = −100 μA		0.2		V	
		V _{DD} = 3 V	I _{OL} = 12 mA	0.8			
			I _{OL} = 6 mA	0.55			
I _{OH}	High-level output current	V _{DD} = 3 V, V _O = 1 V		−28		mA	
		V _{DD} = 3.3 V, V _O = 1.65 V		−36			
		V _{DD} = 3.6 V, V _O = 3.135 V		−14			
I _{OL}	Low-level output current	V _{DD} = 3 V, V _O = 1.95 V		28		mA	
		V _{DD} = 3.3 V, V _O = 1.65 V		36			
		V _{DD} = 3.6 V, V _O = 0.4 V		14			
V _{DD} = 2.5 V ±0.2 V							
V _{OH}	High-level output voltage	V _{DD} = min to max, I _{OH} = −100 μA		V _{DD} − 0.2		V	
		V _{DD} = 2.3 V, I _{OH} = −6 mA		1.8			
V _{OL}	Low-level output voltage	V _{DD} = min to max, I _{OL} = 100 μA		0.2		V	
		V _{DD} = 2.3 V, I _{OL} = 6 mA		0.55			
I _{OH}	High-level output current	V _{DD} = 2.3 V, V _O = 1 V		−15		mA	
		V _{DD} = 2.5 V, V _O = 1.25 V		−25			
		V _{DD} = 2.7 V, V _O = 2.375 V		−10			
I _{OL}	Low-level output current	V _{DD} = 2.3 V, V _O = 1.2 V		15		mA	
		V _{DD} = 2.5 V, V _O = 1.25 V		25			
		V _{DD} = 2.7 V, V _O = 0.3 V		10			

(1) All typical values are at respective nominal V_{DD}.

(2) For I_{CC} over frequency, see [Figure 6](#).

TIMING REQUIREMENTS

over recommended ranges of supply voltage and operating junction temperature

		MIN	NOM	MAX	UNIT
f_{clk}	Clock frequency	$V_{\text{DD}} = 3 \text{ V to } 3.6 \text{ V}$		0	200
		$V_{\text{DD}} = 2.3 \text{ V to } 2.7 \text{ V}$		0	170
					MHz

JITTER CHARACTERISTICS

Characterized using CDCVF2310 Performance EVM when $V_{\text{DD}} = 3.3 \text{ V}$. Outputs not under test are terminated to 50Ω .

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_{jitter}	Additive phase jitter from input to output 1Y0	12 kHz to 5 MHz, $f_{\text{out}} = 30.72 \text{ MHz}$		52	fs rms
		12 kHz to 20 MHz, $f_{\text{out}} = 125 \text{ MHz}$		45	

SWITCHING CHARACTERISTICS

over recommended operating junction temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
$V_{\text{DD}} = 3.3 \text{ V} \pm 0.3 \text{ V}$ (see Figure 2)					
t_{PLH}	CLK to Yn	$f = 0 \text{ MHz to } 200 \text{ MHz}$ For circuit load, see Figure 2.	1.3	3.3	ns
t_{PHL}					
$t_{\text{sk(o)}}$	Output skew (Ym to Yn) ⁽¹⁾ (see Figure 4)			100	ps
$t_{\text{sk(p)}}$	Pulse skew (see Figure 5)			570	ps
$t_{\text{sk(pp)}}$	Part-to-part skew			500	ps
t_{r}	Rise time (see Figure 3)	$V_{\text{O}} = 0.4 \text{ V to } 2 \text{ V}$	0.7	2.2	V/ns
t_{f}	Fall time (see Figure 3)	$V_{\text{O}} = 2 \text{ V to } 0.4 \text{ V}$	0.7	2.2	V/ns
$t_{\text{su(en)}}$	Enable setup time, G_high before CLK ↓		0.1		ns
$t_{\text{su(dis)}}$	Disable setup time, G_low before CLK ↓		0.1		ns
$t_{\text{h(en)}}$	Enable hold time, G_high after CLK ↓		0.4		ns
$t_{\text{h(dis)}}$	Disable hold time, G_low after CLK ↓		0.4		ns
$V_{\text{DD}} = 2.5 \text{ V} \pm 0.2 \text{ V}$ (see Figure 2)					
t_{PLH}	CLK to Yn	$f = 0 \text{ MHz to } 170 \text{ MHz}$ For circuit load, see Figure 2.	1.5	4	ns
t_{PHL}					
$t_{\text{sk(o)}}$	Output skew (Ym to Yn) ⁽¹⁾ (see Figure 4)			170	ps
$t_{\text{sk(p)}}$	Pulse skew (see Figure 5)			680	ps
$t_{\text{sk(pp)}}$	Part-to-part skew			600	ps
t_{r}	Rise time (see Figure 3)	$V_{\text{O}} = 0.4 \text{ V to } 1.7 \text{ V}$	0.5	1.4	V/ns
t_{f}	Fall time (see Figure 3)	$V_{\text{O}} = 1.7 \text{ V to } 0.4 \text{ V}$	0.5	1.4	V/ns
$t_{\text{su(en)}}$	Enable setup time, G_high before CLK ↓		0.1		ns
$t_{\text{su(dis)}}$	Disable setup time, G_low before CLK ↓		0.1		ns
$t_{\text{h(en)}}$	Enable hold time, G_high after CLK ↓		0.4		ns
$t_{\text{h(dis)}}$	Disable hold time, G_low after CLK ↓		0.4		ns

(1) The $t_{\text{sk(o)}}$ specification is only valid for equal loading of all outputs.

DETAILED DESCRIPTION

Output Enable Glitch Suppression Circuit

The purpose of the glitch suppression circuitry is to ensure the output enable sequence is synchronized with the clock input such that the output buffer is enabled or disabled on the next full period of the input clock (negative edge triggered by the input clock) (see [Figure 1](#)).

The G input must fulfill the timing requirements (t_{su} , t_h) according to the *Switching Characteristics* table for predictable operation.

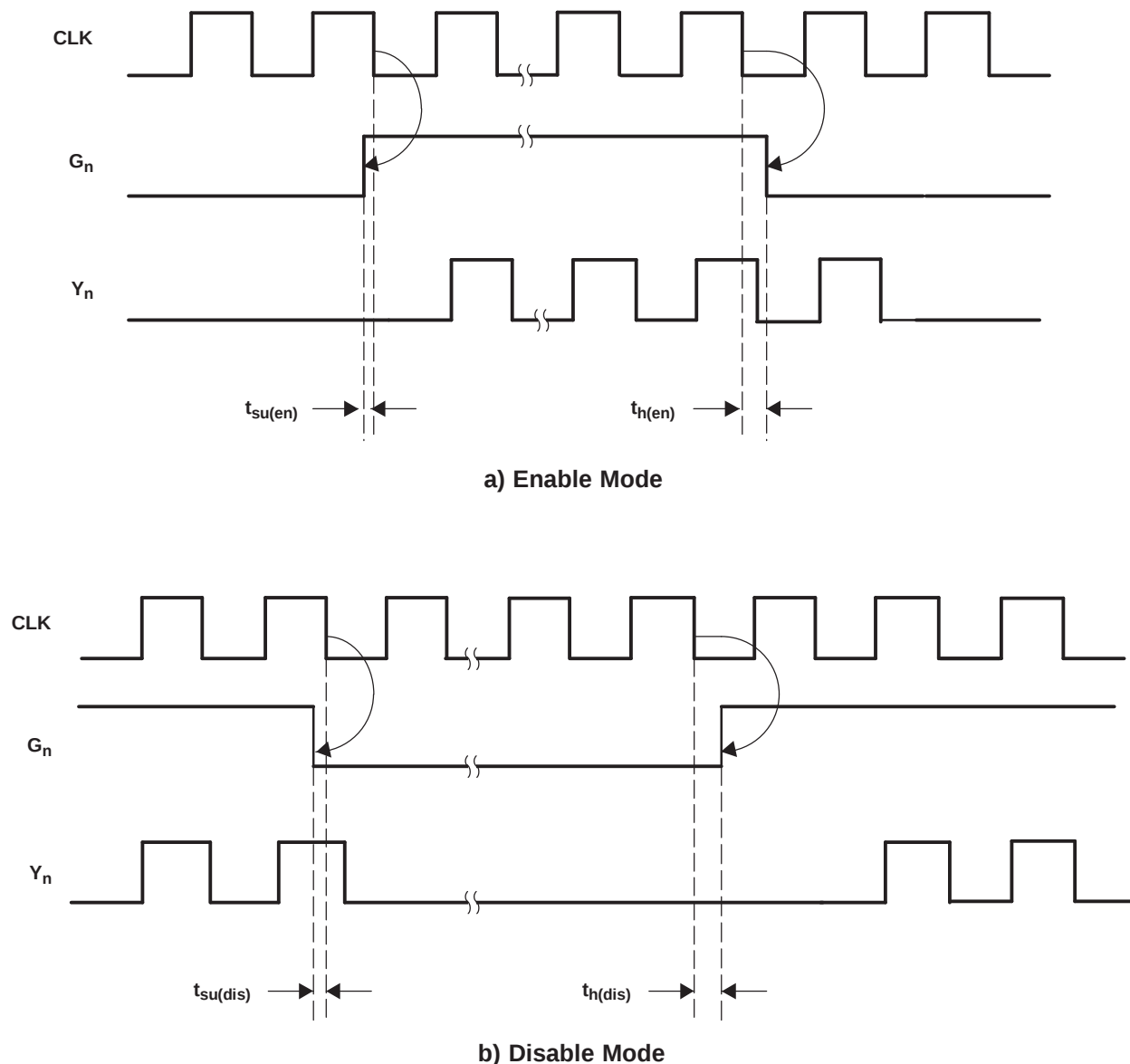
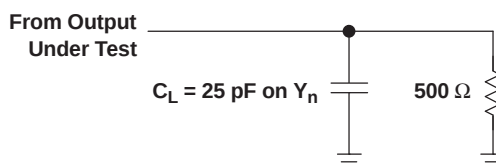


Figure 1. Enable and Disable Mode Relative to CLK↓

PARAMETER MEASUREMENT INFORMATION



- C_L includes probe and jig capacitance.
- All input pulses are supplied by generators having the following characteristics: $\text{PRR} \leq 200 \text{ MHz}$, $Z_O = 50 \Omega$, $t_r < 1.2 \text{ ns}$, $t_f < 1.2 \text{ ns}$.

Figure 2. Test Load Circuit

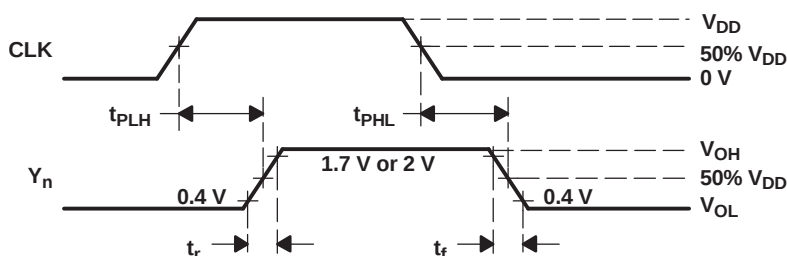


Figure 3. Voltage Waveforms Propagation Delay Times

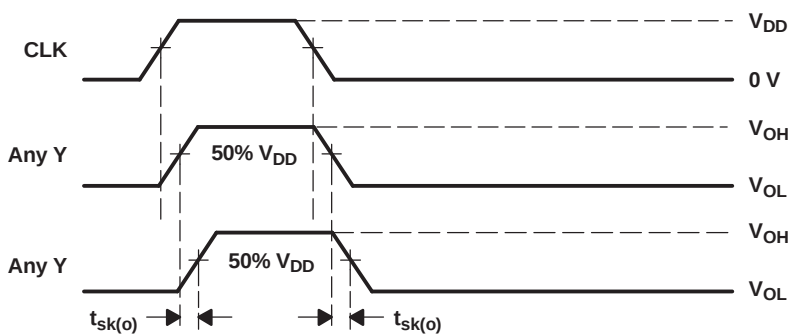
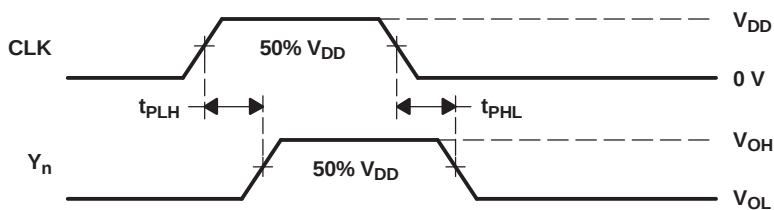


Figure 4. Output Skew



NOTE: $t_{sk(p)} = |t_{PLH} - t_{PHL}|$

Figure 5. Pulse Skew

PARAMETER MEASUREMENT INFORMATION (continued)

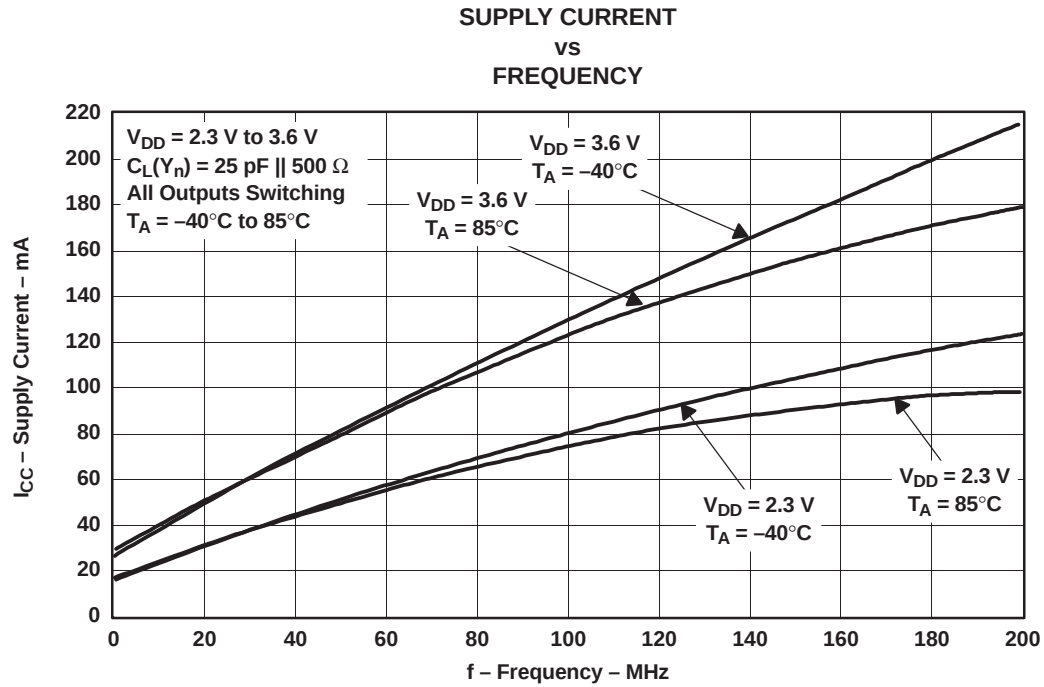


Figure 6.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish	MSL Peak Temp (3)	Op Temp (°C)	Top-Side Markings (4)	Samples
CDCVF2310MPWEP	ACTIVE	TSSOP	PW	24	60	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-55 to 125	CKV2310EP	Samples
CDCVF2310MPWREP	ACTIVE	TSSOP	PW	24	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-55 to 125	CKV2310EP	Samples
V62/13603-01XE	ACTIVE	TSSOP	PW	24	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-55 to 125	CKV2310EP	Samples
V62/13603-01XE-T	ACTIVE	TSSOP	PW	24	60	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-55 to 125	CKV2310EP	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBsolete: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check <http://www.ti.com/productcontent> for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) Multiple Top-Side Markings will be inside parentheses. Only one Top-Side Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Top-Side Marking for that device.

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OTHER QUALIFIED VERSIONS OF CDCVF2310-EP :

- Catalog: [CDCVF2310](#)

NOTE: Qualified Version Definitions:

- Catalog - TI's standard catalog product



PW0024A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



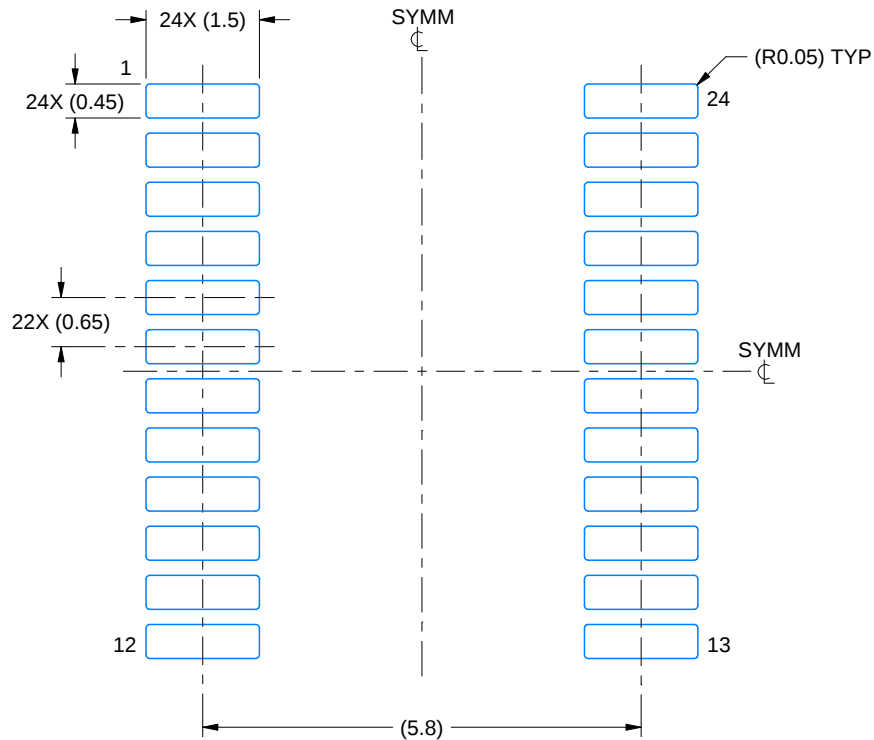
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-153.

EXAMPLE BOARD LAYOUT

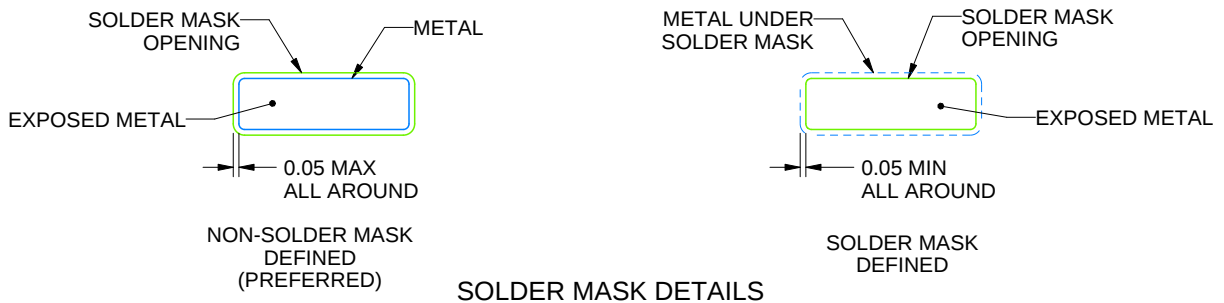
PW0024A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 10X



SOLDER MASK DETAILS

4220208/A 02/2017

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

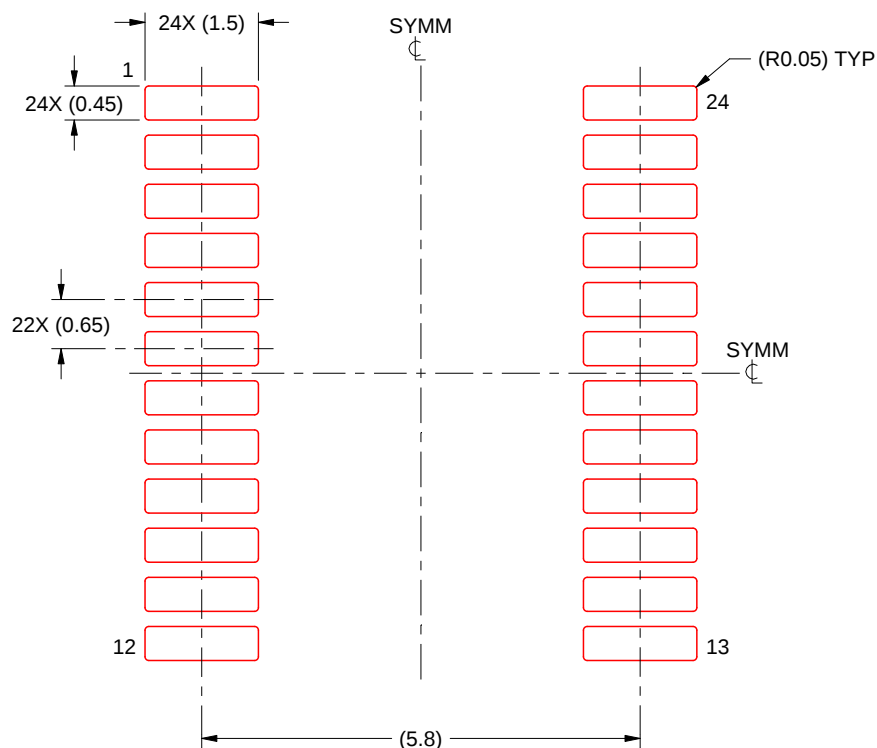
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

PW0024A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 10X

4220208/A 02/2017

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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